

|              |         |  |
|--------------|---------|--|
| <b>SANYO</b> | No.2093 | 2 S A 1 4 7 9 / 2 S C 3 7 8 9  |
|              |         | PNP/NPN Epitaxial Planar Type<br>Silicon Transistors<br>HIGH-DEFINITION CRT DISPLAY<br>VIDEO OUTPUT APPLICATIONS |

**Applications**

- High-definition CRT display
- Color TV chroma output, high breakdown voltage drivers

**Features**

- High breakdown voltage ( $V_{CE0} \geq 300V$ )
- Excellent high frequency characteristic ( $c_{re} = 1.8pF(\text{typ})$ )
- Adoption of MBIT process
- No insulator required for mounting, which contributes to reducing the cost and the number of manufacturing processes.
- Plastic-covered heat sink facilitating high-density mounting
- Directly interchangeable with TO-126 because the package is designed based on the conventional package dimensions

( ): 2SA1479

**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

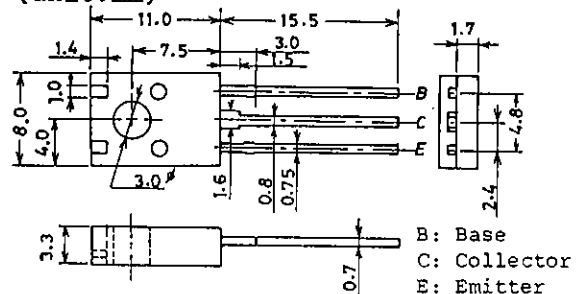
|                              |           |                    | unit       |
|------------------------------|-----------|--------------------|------------|
| Collector-to-Base Voltage    | $V_{CB0}$ | (-)300             | V          |
| Collector-to-Emitter Voltage | $V_{CE0}$ | (-)300             | V          |
| Emitter-to-Base Voltage      | $V_{EB0}$ | (-)5               | V          |
| Collector Current            | $I_C$     | (-)100             | mA         |
| Peak Collector Current       | $i_{cp}$  | (-)200             | mA         |
| Collector Dissipation        | $P_C$     | 1.5                | W          |
|                              |           | $T_c = 25^\circ C$ | 7          |
| Junction Temperature         | $T_j$     | 150                | $^\circ C$ |
| Storage Temperature          | $T_{stg}$ | -55 to +150        | $^\circ C$ |

**Electrical Characteristics at  $T_a = 25^\circ C$**

|                          |               |                                  | min | typ | max    | unit    |
|--------------------------|---------------|----------------------------------|-----|-----|--------|---------|
| Collector Cutoff Current | $I_{CBO}$     | $V_{CB} = (-)200V, I_E = 0$      |     |     | (-)0.1 | $\mu A$ |
| Emitter Cutoff Current   | $I_{EBO}$     | $V_{EB} = (-)4V, I_C = 0$        |     |     | (-)0.1 | $\mu A$ |
| DC Current Gain          | $h_{FE}$      | $V_{CE} = (-)10V, I_C = (-)10mA$ | 40* |     | 320*   |         |
| Gain-Bandwidth Product   | $f_T$         | $V_{CE} = (-)30V, I_C = (-)10mA$ |     | 70  |        | MHz     |
| C-E Saturation Voltage   | $V_{CE(sat)}$ | $I_C = (-)20mA, I_B = (-)2mA$    |     |     | (-)0.6 | V       |
| B-E Saturation Voltage   | $V_{BE(sat)}$ | $I_C = (-)20mA, I_B = (-)2mA$    |     |     | (-)1.0 | V       |

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**Package Dimensions 2042A**  
(unit:mm)



SANYO: TO126ML

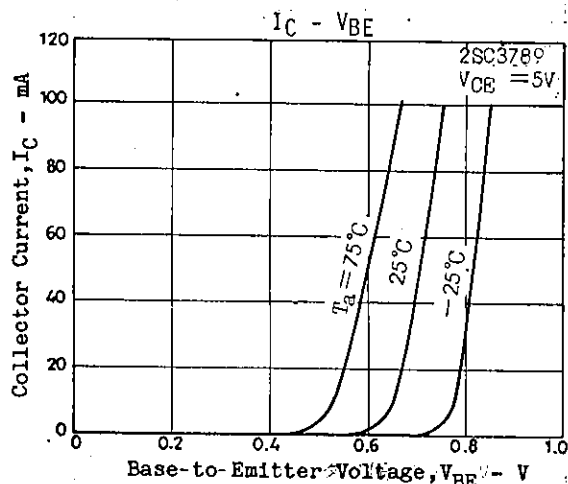
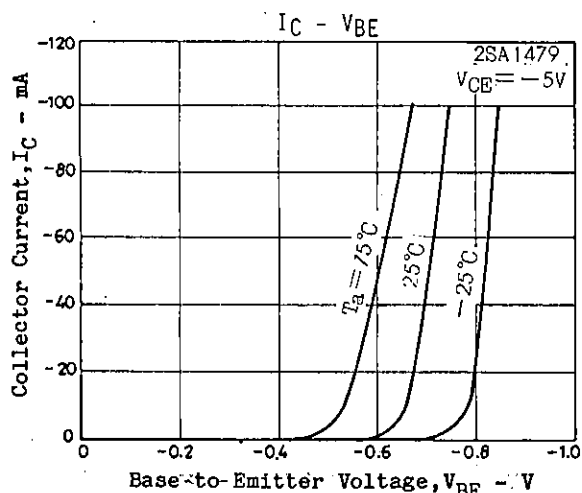
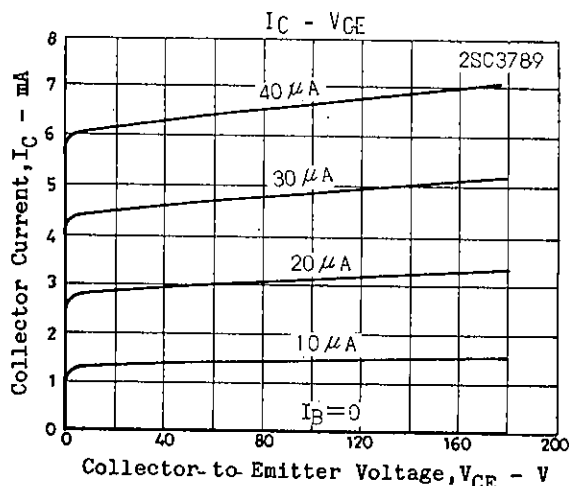
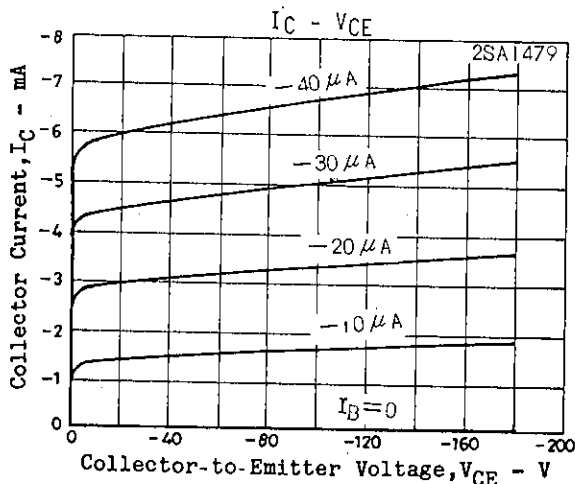
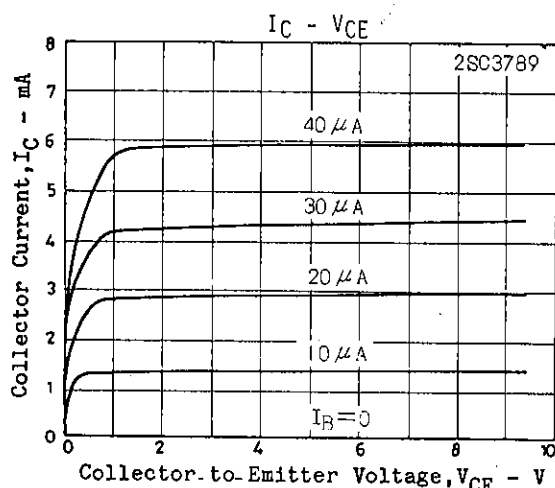
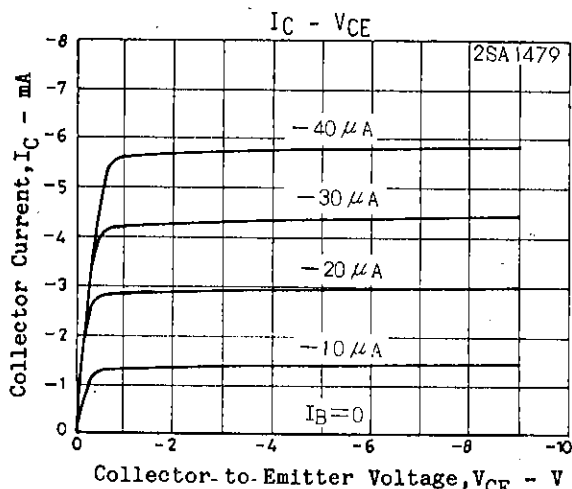
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TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

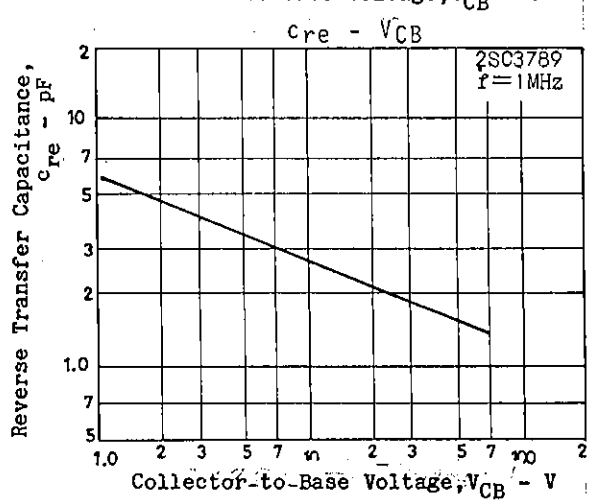
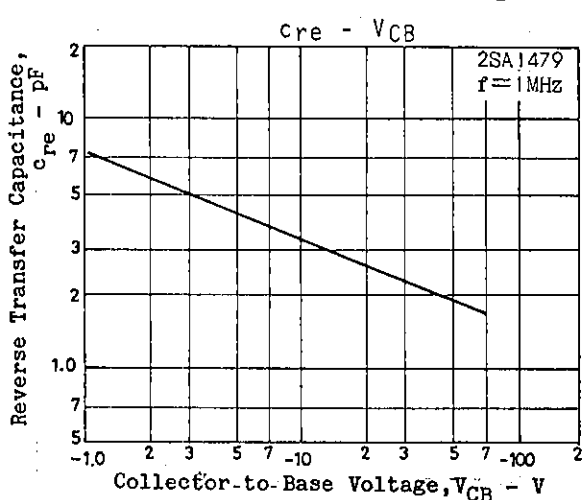
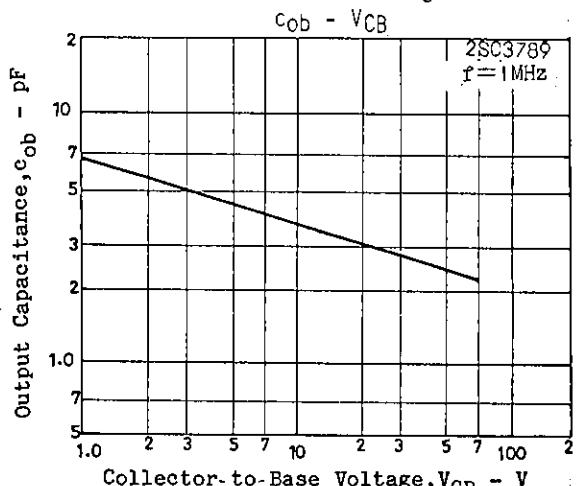
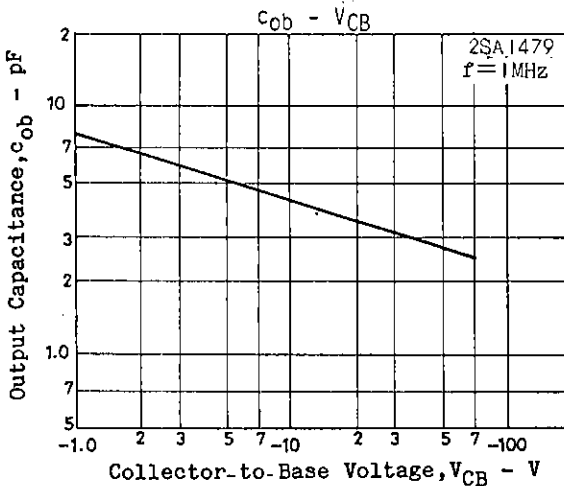
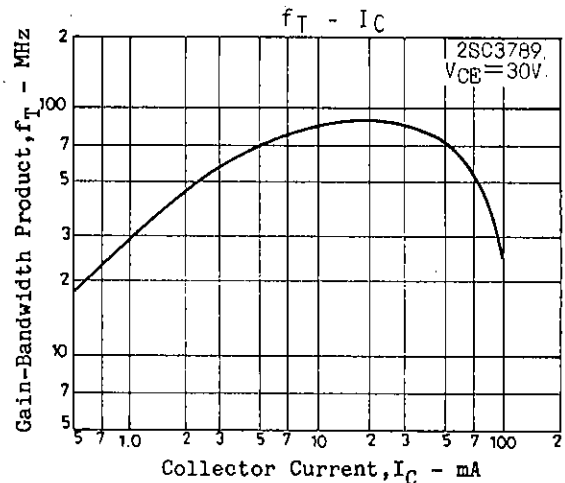
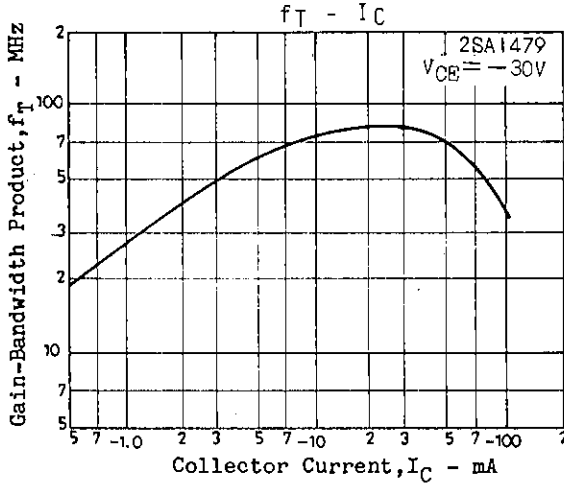
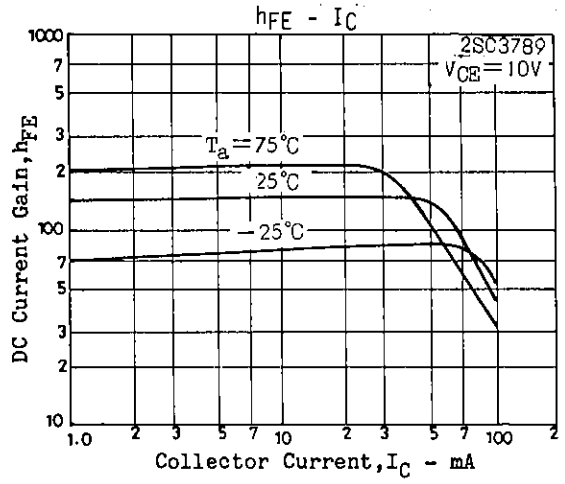
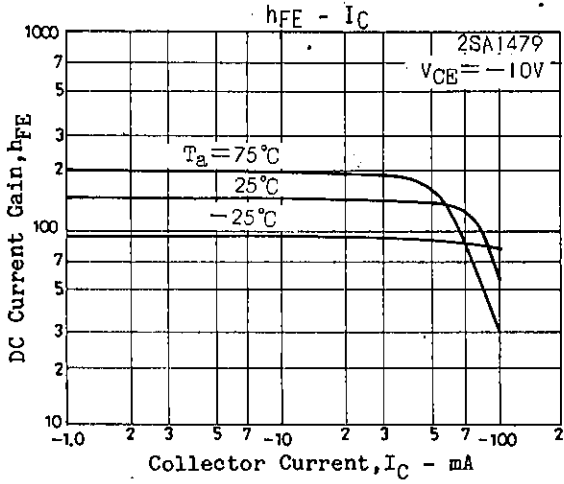
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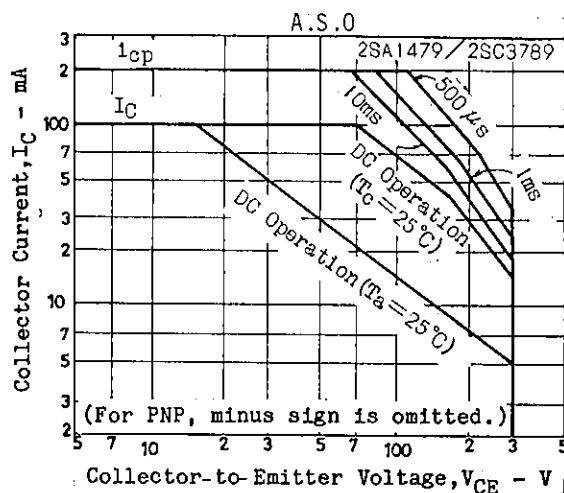
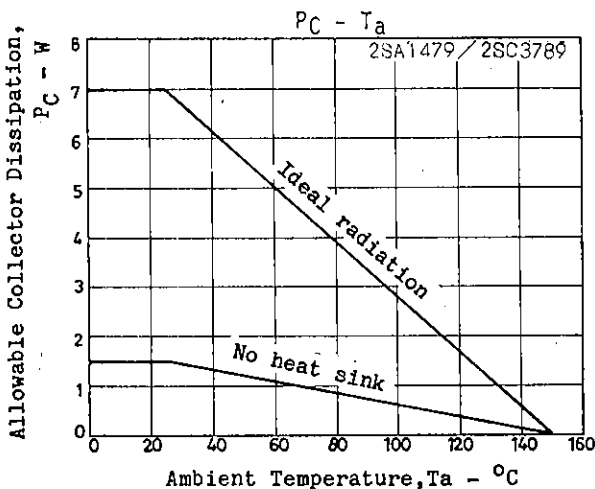
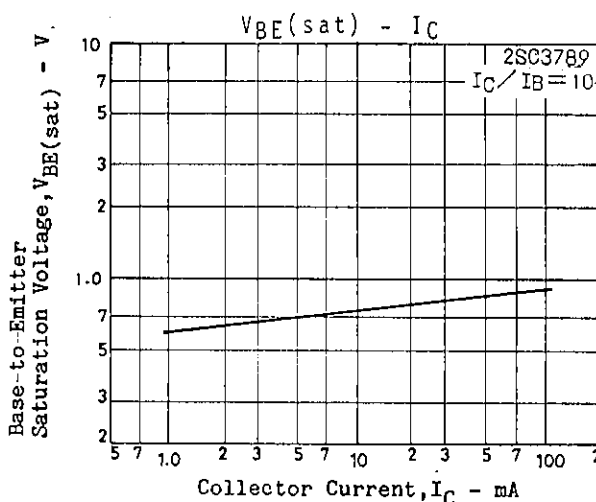
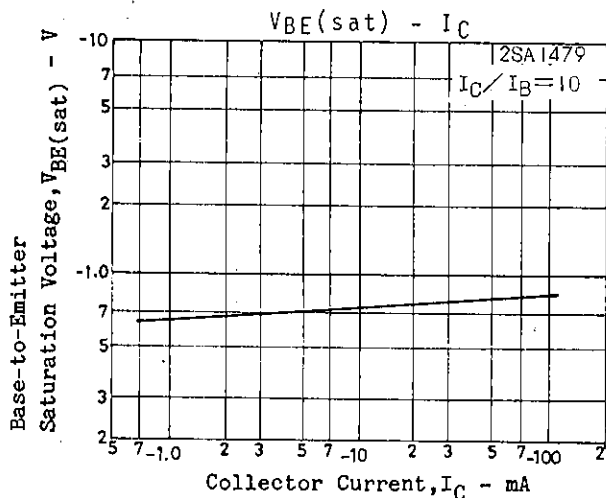
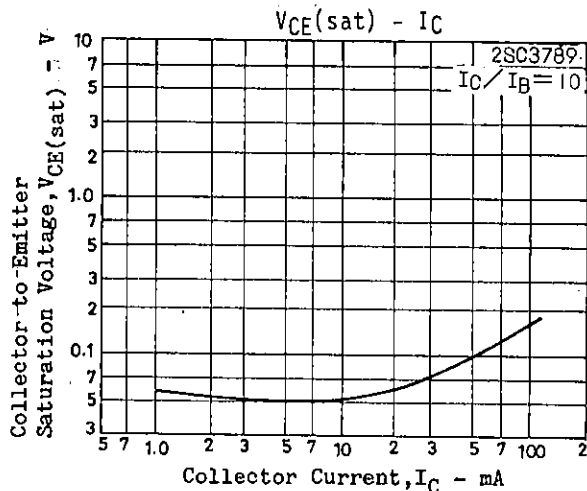
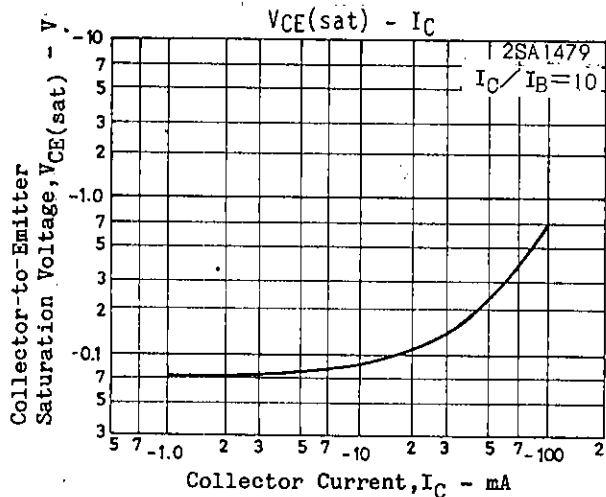
|                              |               |                             | min    | typ          | max | unit |
|------------------------------|---------------|-----------------------------|--------|--------------|-----|------|
| C-B Breakdown Voltage        | $V_{(BR)CBO}$ | $I_C=(-)10\mu A, I_E=0$     | (-)300 |              |     | V    |
| C-E Breakdown Voltage        | $V_{(BR)CEO}$ | $I_E=(-)1mA, R_{BE}=\infty$ | (-)300 |              |     | V    |
| E-B Breakdown Voltage        | $V_{(BR)EBO}$ | $I_E=(-)10\mu A, I_C=0$     | (-)5   |              |     | V    |
| Output Capacitance           | $c_{ob}$      | $V_{CB}=(-)30V, f=1MHz$     |        | 2.6<br>(3.1) |     | pF   |
| Reverse Transfer Capacitance | $c_{re}$      | $V_{CB}=(-)30V, f=1MHz$     |        | 1.8<br>(2.3) |     | pF   |

\*: The 2SA1479/2SC3789 are classified by 10mA  $h_{FE}$  as follows:

|    |   |    |    |   |     |     |   |     |     |   |     |
|----|---|----|----|---|-----|-----|---|-----|-----|---|-----|
| 40 | C | 80 | 60 | D | 120 | 100 | E | 200 | 160 | F | 320 |
|----|---|----|----|---|-----|-----|---|-----|-----|---|-----|







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